

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (Currently Amended): A non-volatile semiconductor memory device comprising:

a semiconductor body of a first conductivity type;

first and second semiconductor regions of a second conductivity type, formed apart from each other on the semiconductor body;

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a stacked gate formed on the semiconductor body between the first and second semiconductor regions, with a gate insulating film inserted therebetween, the stacked gate having a first side surface, a second side surface opposed to the first side surface, and an upper surface;

an interlayer insulating film formed above the semiconductor body;

a contact material buried to be adjacent to the first side surface of the stacked gate in the interlayer insulating film, the contact material contacting the first semiconductor region;

a first insulating film formed on the second side surface and on the upper surface, but not on the first side surface of the stacked gate adjacent to the contact material; and

a second insulating film formed on the first side surface adjacent to the contact material, the second insulating film having an etch rate slower than that of said first insulating film and covering the entirety of the first insulating film.

Claim 2 (Original): The device according to claim 1, wherein the stacked gate includes a charge storage layer on the gate insulating film, a control gate on the charge

storage layer, a cap insulating film on the control gate, and the first side surface of the stacked gate includes side surfaces of the charge storage layer, the control gate, and the cap insulating film.

Claim 3 (Original): The device according to claim 2, wherein the first insulating film is made of a material different from the cap insulating film, and the second insulating film is made of the same material as the cap insulating film.

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Claim 4 (Original): The device according to claim 2, wherein the contact material has a side surface, the side surface contacts the second insulating film, and a part of the side surface extends over the cap insulating film.

Claim 5 (Previously Amended): The device according to claim 1, wherein the first insulating film is an oxide-based insulating film having a film thickness of 100 to 200 , and the second insulating film is a nitride-based insulating film having a film thickness of 200 to 400 .

Claim 6 (Currently Amended): A non-volatile semiconductor memory device comprising:

a semiconductor body of a first conductivity type;
first and second semiconductor regions of a second conductivity type, formed apart from each other on the semiconductor body;

a stacked gate formed on the semiconductor body between the first and second semiconductor regions, with a gate insulating film inserted therebetween, the stacked gate including a charge storage layer on the gate insulating film, a control gate on the charge storage layer, and a cap insulating film on the control gate, and the stacked gate having a first side surface, a second side surface opposed to the first side surface, and an upper surface, the first and second surfaces each including side surfaces of the charge storage layer, the control gate, and the cap insulating film;

an interlayer insulating film formed above the semiconductor body;

a contact material buried to be adjacent to the first side surface of the stacked gate in the interlayer insulating film, the contact material contacting the first semiconductor region;

a first insulating film formed on the side surface of the control gate on the first side surface, and on all of the side surface of the charge storage layer on the first side surface; and

a second insulating film formed on the first side surface adjacent to the contact material, the second insulating film having an etch rate slower than that of said first insulating film and covering the entirety of the first insulating film.

Claim 7 (Original): The device according to claim 6, wherein the first insulating film is made of a material different from the cap insulating film, and the second insulating film is made of the same material as the cap insulating film.

Claim 8 (Original): The device according to claim 6, wherein the contact material has a side surface, the side surface contacts the second insulating film, and a part of the side surface extends over the cap insulating film.

Claim 9 (Previously Amended): The device according to claim 6, wherein the first insulating film is an oxide-based insulating film having a film thickness of 100 to 200 , and the second insulating film is a nitride-based insulating film having a film thickness of 200 to 400 .

Claim 10 (Currently Amended): A non-volatile semiconductor memory device comprising:

B3 a semiconductor body of a first conductivity type;

first and second semiconductor regions of a second conductivity type, formed apart from each other on the semiconductor body;

a stacked gate formed on the semiconductor body between the first and second semiconductor regions, with a gate insulating film inserted therebetween, the stacked gate including a charge storage layer on the gate insulating film, a control gate on the charge storage layer, and a cap insulating film on the control gate, and the stacked gate having a first side surface, a second side surface opposed to the first side surface, and an upper surface, the first and second surfaces each including side surfaces of the charge storage layer, the control gate, and the cap insulating film;

an interlayer insulating film formed above the semiconductor body;

a contact material buried to be adjacent to the first side surface of the stacked gate in the interlayer insulating film, the contact material contacting the first semiconductor region;

a first insulating film formed on the side surface of the control gate on the first side surface, on all of the side surface of the charge storage layer on the first side surface, on the

side surface of the control gate on the second side surface, and on all of the side surface of the charge storage layer on the second side surface; and

a second insulating film formed on the first side surface adjacent to the contact material, the second insulating film having an etch rate slower than that of said first insulating film and covering the entirety of the first insulating film, the second insulating film being formed on the second side surface, and covering the entirety of the first insulating film and the upper surface.

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Claim 11 (Original): The device according to claim 10, wherein the first insulating film is made of a material different from the cap insulating film, and the second insulating film is made of the same material as the cap insulating film.

Claim 12 (Original): The device according to claim 10, wherein the contact material has a side surface, the side surface contacts the second insulating film, and a part of the side surface extends over the cap insulating film.

Claim 13 (Previously Amended): The device according to claim 10, wherein the first insulating film is an oxide-based insulating film having a film thickness of 100 to 200 , and the second insulating film is a nitride-based insulating film having a film thickness of 200 to 400 .

Claim 14-18 (Withdrawn)

--Claim 19 (New): A non-volatile semiconductor memory device comprising:

a semiconductor body of a first conductivity type;

first and second semiconductor regions of a second conductivity type, formed apart from each other on the semiconductor body;

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a stacked gate formed on the semiconductor body between the first and second semiconductor regions, with a gate insulating film inserted therebetween, the stacked gate having a first side surface, a second side surface opposed to the first side surface, and an upper surface;

an interlayer insulating film formed above the semiconductor body;

a contact material buried to be adjacent to the first side surface of the stacked gate in the interlayer insulating film, the contact material contacting the first semiconductor region;

a first insulating film made from silicon oxide, formed on the second side surface and on the upper surface, but not on the first side surface of the stacked gate adjacent to the contact material; and

a second insulating film made from silicon nitride, formed on the first side surface adjacent to the contact material, the second insulating film covering the entirety of the first insulating film.--
